

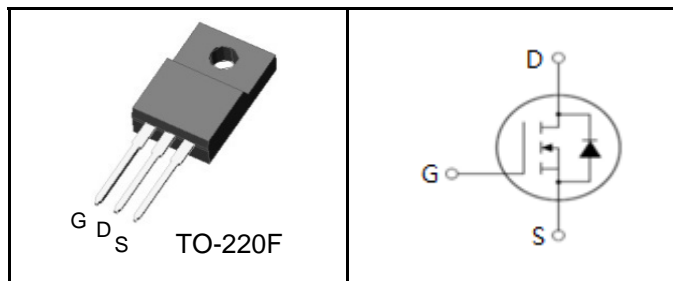
650V Super-Junction Power MOSFET

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant
- Ultra-fast body diode
- Very high commutation ruggedness

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Resonant switching stages



Device Marking and Package Information

Device	Package	Marking
MPSA65M180CFD	TO-220F	MP65M180CFD

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	650	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current (note1)	I_{DM}	60	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	605	mJ
Repetitive Avalanche Current (note1)	I_{AR}	6	A
Repetitive Avalanche Energy (note1)	E_{AR}	0.7	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 400\text{V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 400\text{V}$, $I_{SD} \leq I_D$	dv/dt	50	V/ns
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	34	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	3.9	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

MPSA65M180CFD

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	2	μA
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	500	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	--	5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$	--	0.158	0.180	Ω
Gate Resistance	R_G	$f = 1.0\text{MHz}$, open drain	--	8	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	1947	--	pF
Output Capacitance	C_{oss}		--	64	--	
Reverse Transfer Capacitance	C_{rss}		--	6	--	
Total Gate Charge	Q_g	$V_{DD} = 400V, I_D = 20A,$ $V_{GS} = 10V$	--	42	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	
Gate-Drain Charge	Q_{gd}		--	15	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 20A,$ $V_{GS} = 10V, R_G = 25\Omega$	--	15	--	ns
Turn-on Rise Time	t_r		--	59	--	
Turn-off Delay Time	$t_{d(off)}$		--	121	--	
Turn-off Fall Time	t_f		--	44	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	20	A
Pulsed Diode Forward Current	I_{SM}		--	--	60	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 10A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = 20A,$ $di_F/dt = 100A/\mu s$	--	120	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.52	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	8.4	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 6A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

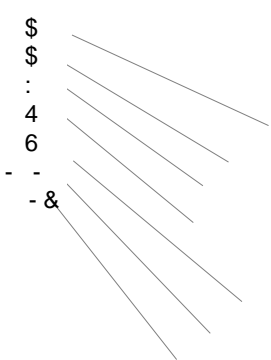
MPSA65M180CFD

&! (' % (+%,! 4(/

!87

!\$ %) ' % (%! ! (

5 2 % # 1 % ' %\$ (% %! ! (



!8

, \$

+; , -.

=

!

+; , -\$.

/ 0 0

! "

5 / 5 0 0

! "

!\$ % 6 2 # * ! # (. 2 - % ! # % % #

!\$

\$

5 , \$
+; , -.

\$

\$

\$

\$

H⁵ , \$
(I

\$

/ 7 !8"

/ 0 0 ! "

!\$ % 2 3 0 & -! 0 % , % 0 \$

!8

\$

+; , -.

\$

+; , -.

7

\$

/

\$

/ 0 0 ! "

&) ! (' % (+ % ! 4 (

! \$ % 2 # * ! # (. 2
+ # (! # ") % %

! \$ % ; 2 ' % ' 0 \$. 2
+ # (! # ") % %

| ' "

5 , \$
7 , \$ 8

=

7 , - \$ C 8

| "/ ! 2

5 | "/ !

;/ ; + 4 " !

;/ ; + 4 "+ !

! N < "

! \$ % 9 2 % # ! # ' % " ") 0 # (

\$

7

\$

D ; / +

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

\$

+ /)

-

!

=

-

Figure A: Gate Charge Test Circuit and Waveform

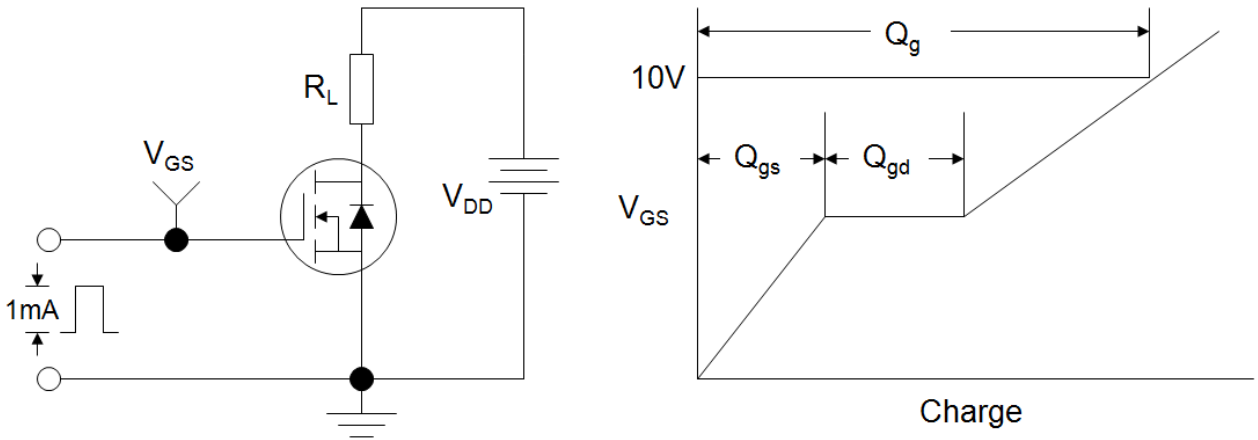


Figure B: Resistive Switching Test Circuit and Waveform

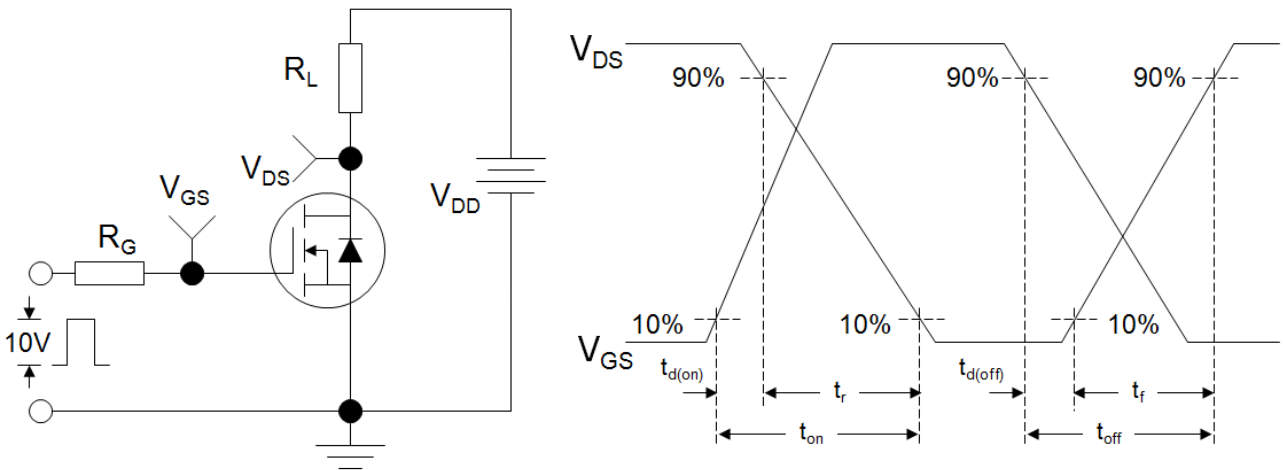
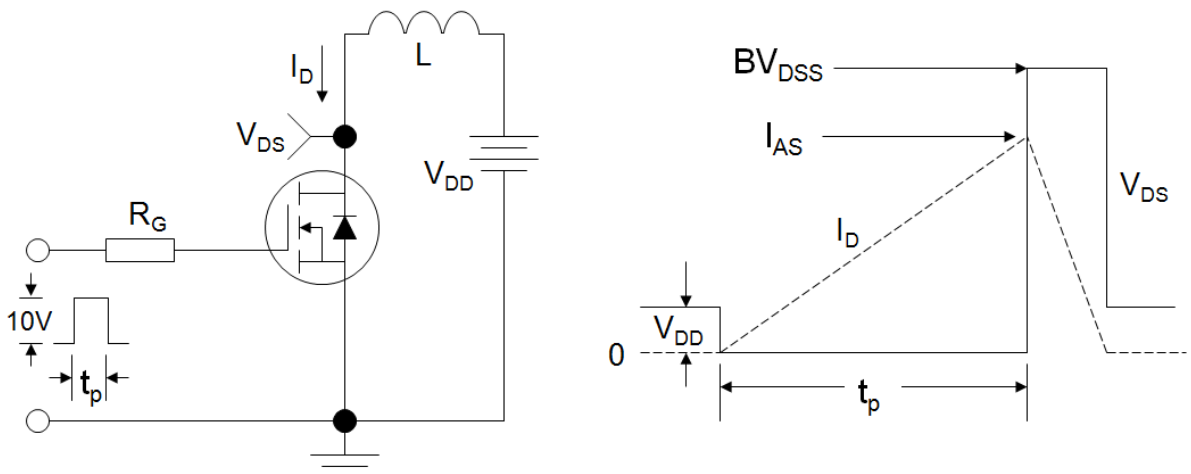


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



Package Dimension

unit: mm

